

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	359244	(flash (non near3 volatile) eeprom eeprom e2prom)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/13 17:10
L2	83633	1 and (float\$3 ner5 gate)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/13 17:10
L3	24217	2 and (control near5 gate)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/13 17:11
L4	4390	3 and (thermal\$3 near5 (oxide oxidation oxidizing))	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/13 17:11
L5	4192	4 and (etch\$3 pattern\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/13 16:42
L6	4179	5 and (silicon polysilicon)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/13 16:42
L7	4121	6 and (dielectric insulat\$3)	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/13 16:44
L8	1422	7 and (side near5 (surface sidewall))	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/13 16:44
L9	1330	3 and ((thermal\$3 near5 (oxide oxidation oxidizing)) same (first near5 (silicon polysilicon)))	US-PGPU B; USPAT; USOCR	OR	ON	2005/05/13 16:48
L10	117667	(flash (non near3 volatile) eeprom eeprom e2prom)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/13 17:10
L11	16988	10 and (float\$3 ner5 gate)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/13 17:10
L12	7083	11 and (control near5 gate)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/13 17:11
L13	221	12 and (thermal\$3 near5 (oxide oxidation oxidizing))	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/05/13 17:11